

## SINGLE 2-INPUT OPEN DRAIN NAND GATE

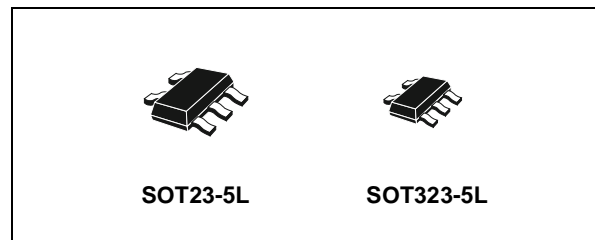
- HIGH SPEED:  $t_{PD} = 5.4ns$  (TYP.) at  $V_{CC} = 5V$
- LOW POWER DISSIPATION:  
 $I_{CC} = 1\mu A$ (MAX.) at  $T_A=25^\circ C$
- COMPATIBLE WITH TTL OUTPUTS:  
 $V_{IH} = 2V$  (MIN),  $V_{IL} = 0.8V$  (MAX)
- POWER DOWN PROTECTION ON INPUTS
- OPERATING VOLTAGE RANGE:  
 $V_{CC}(OPR) = 4.5V$  to  $5.5V$
- IMPROVED LATCH-UP IMMUNITY

### DESCRIPTION

The 74V1T03 is an advanced high-speed CMOS SINGLE 2-INPUT OPEN DRAIN NAND GATE fabricated with sub-micron silicon gate and double-layer metal wiring C<sup>2</sup>MOS technology.

The internal circuit is composed of 3 stages including buffer output, which provide high noise immunity and stable output.

The device can, with an external pull-up resistor, be used in wired AND configuration. This device



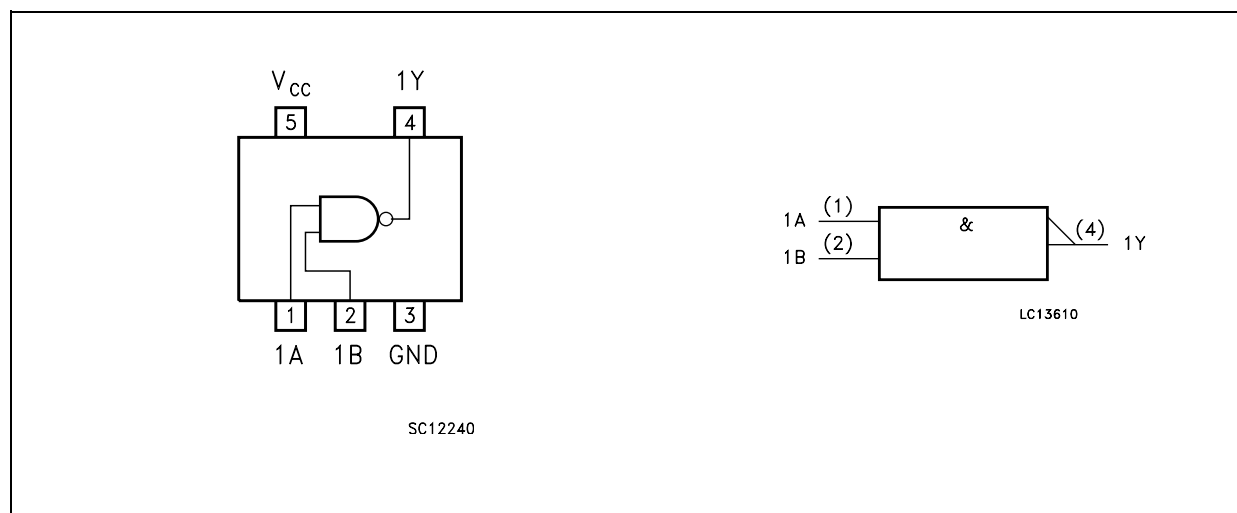
### ORDER CODES

PACKAGE	T & R
SOT23-5L	74V1T03STR
SOT323-5L	74V1T03CTR

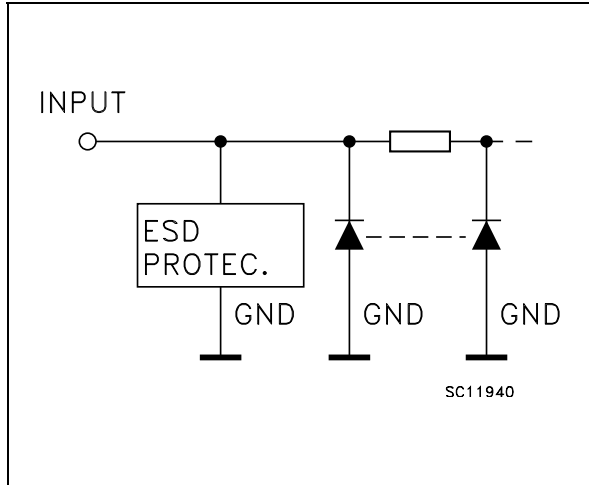
can also be used as a led driver in any other application requiring current sink.

Power down protection is provided on all inputs and 0 to 7V can be accepted on inputs with no regard to the supply voltage. This device can be used to interface 5V to 3V.

### PIN CONNECTION AND IEC LOGIC SYMBOLS



**INPUT EQUIVALENT CIRCUIT**



**PIN DESCRIPTION**

PIN N°	SYMBOL	NAME AND FUNCTION
1	1A	Data Input
2	1B	Data Input
4	1Y	Data Output
3	GND	Ground (0V)
5	V <sub>CC</sub>	Positive Supply Voltage

**TRUTH TABLE**

A	B	Y
L	L	Z
L	H	Z
H	L	Z
H	H	L

Z: High Impedance State

**ABSOLUTE MAXIMUM RATINGS**

Symbol	Parameter	Value	Unit
V <sub>CC</sub>	Supply Voltage	-0.5 to +7.0	V
V <sub>I</sub>	DC Input Voltage	-0.5 to +7.0	V
V <sub>O</sub>	DC Output Voltage	-0.5 to V <sub>CC</sub> + 0.5	V
I <sub>IK</sub>	DC Input Diode Current	- 20	mA
I <sub>OK</sub>	DC Output Diode Current	± 20	mA
I <sub>O</sub>	DC Output Current	+ 25	mA
I <sub>CC</sub> or I <sub>GND</sub>	DC V <sub>CC</sub> or Ground Current	± 50	mA
T <sub>stg</sub>	Storage Temperature	-65 to +150	°C
T <sub>L</sub>	Lead Temperature (10 sec)	260	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied.

**RECOMMENDED OPERATING CONDITIONS**

Symbol	Parameter	Value	Unit
V <sub>CC</sub>	Supply Voltage	4.5 to 5.5	V
V <sub>I</sub>	Input Voltage	0 to 5.5	V
V <sub>O</sub>	Output Voltage	0 to V <sub>CC</sub>	V
T <sub>op</sub>	Operating Temperature	-55 to 125	°C
dt/dv	Input Rise and Fall Time (note 1) (V <sub>CC</sub> = 5.0 ± 0.5V)	0 to 20	ns/V

1) V<sub>IN</sub> from 0.8V to 2V

## DC SPECIFICATIONS

Symbol	Parameter	Test Condition		Value						Unit	
		V <sub>CC</sub> (V)		T <sub>A</sub> = 25°C			-40 to 85°C		-55 to 125°C		
				Min.	Typ.	Max.	Min.	Max.	Min.		Max.
V <sub>IH</sub>	High Level Input Voltage	4.5 to 5.5		2			2		2		V
V <sub>IL</sub>	Low Level Input Voltage	4.5 to 5.5				0.8		0.8		0.8	V
V <sub>OL</sub>	Low Level Output Voltage	4.5	I <sub>O</sub> =50 μA		0.0	0.1		0.1		0.1	V
		4.5	I <sub>O</sub> =8 mA			0.36		0.44		0.55	
I <sub>OZ</sub>	High Impedance Output Leakage Current	5.5	V <sub>I</sub> = V <sub>IH</sub> or V <sub>IL</sub> V <sub>O</sub> = V <sub>CC</sub> or GND			±0.25		± 2.5		± 5.0	μA
I <sub>I</sub>	Input Leakage Current	0 to 5.5	V <sub>I</sub> = 5.5V or GND			± 0.1		± 1.0		± 1.0	μA
I <sub>CC</sub>	Quiescent Supply Current	5.5	V <sub>I</sub> = V <sub>CC</sub> or GND			1		10		20	μA
+I <sub>CC</sub>	Additional Worst Case Supply Current	5.5	One Input at 3.4V, other input at V <sub>CC</sub> or GND			1.35		1.5		1.5	mA

AC ELECTRICAL CHARACTERISTICS (Input t<sub>r</sub> = t<sub>f</sub> = 3ns)

Symbol	Parameter	Test Condition		Value						Unit	
		V <sub>CC</sub> (V)	C <sub>L</sub> (pF)	T <sub>A</sub> = 25°C			-40 to 85°C		-55 to 125°C		
				Min.	Typ.	Max.	Min.	Max.	Min.		Max.
t <sub>pZL</sub>	Enable Delay Time	5.0 (*)	15		3.7	7.0	1.0	8.0	1.0	9.0	ns
		5.0 (*)	50		4.1	8.0	1.0	9.0	1.0	10.0	
t <sub>pLZ</sub>	Disable Delay Time	5.0 (*)	15		5.4	7.0	1.0	8.0	1.0	9.0	ns
		5.0 (*)	50		5.9	8.0	1.0	9.0	1.0	10.0	

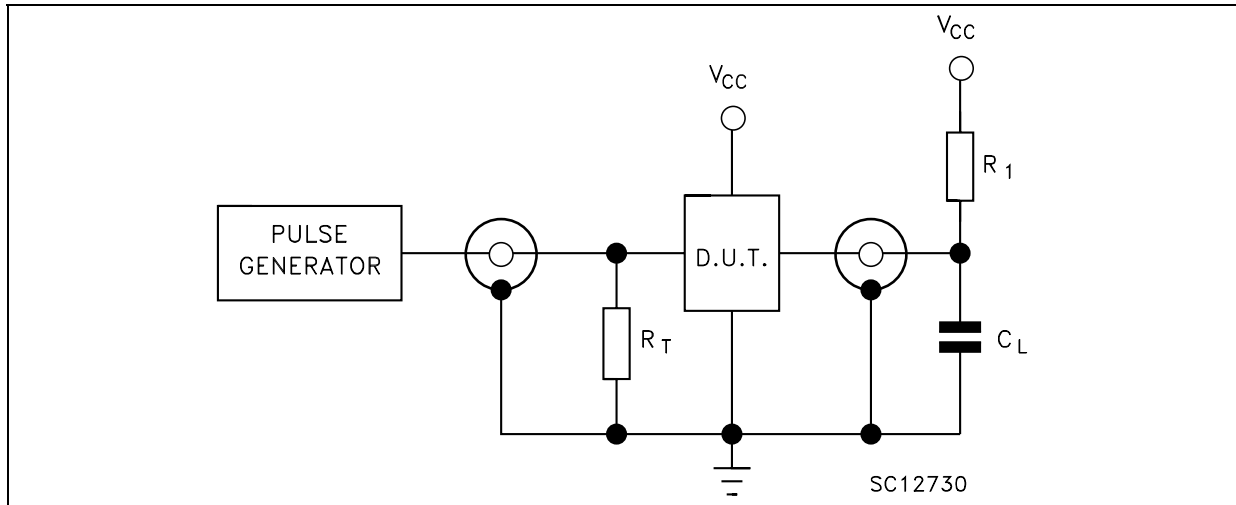
(\*) Voltage range is 5.0V ± 0.5V

## CAPACITIVE CHARACTERISTICS

Symbol	Parameter	Test Condition		Value						Unit	
				T <sub>A</sub> = 25°C			-40 to 85°C		-55 to 125°C		
				Min.	Typ.	Max.	Min.	Max.	Min.		Max.
C <sub>IN</sub>	Input Capacitance				4	10		10		10	pF
C <sub>OUT</sub>	Output Capacitance				5	10		10		10	pF
C <sub>PD</sub>	Power Dissipation Capacitance (note 1)				6						pF

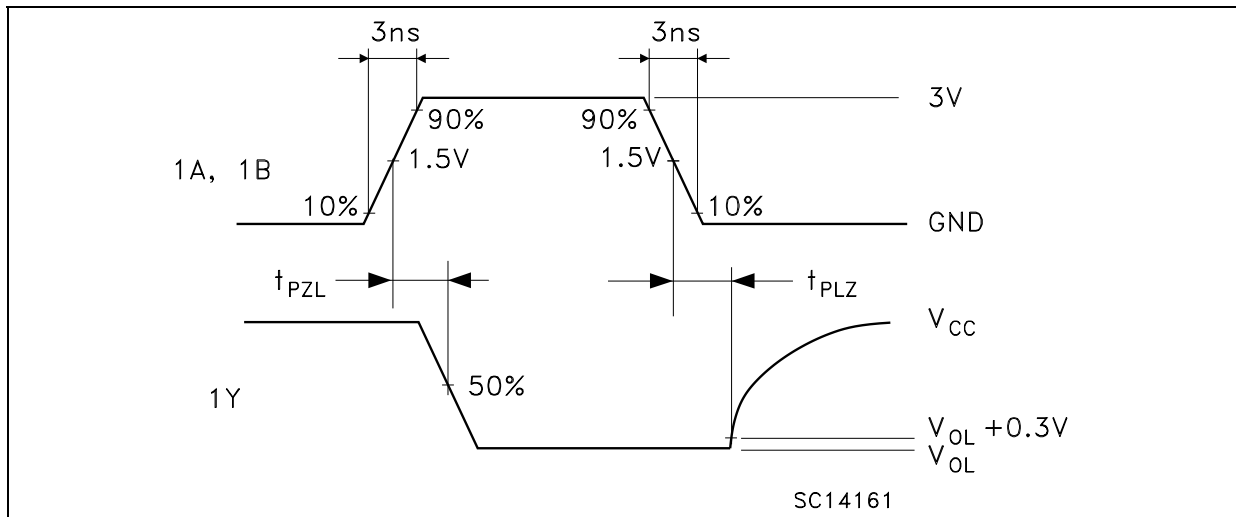
1) C<sub>PD</sub> is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. (Refer to Test Circuit). Average operating current can be obtained by the following equation. I<sub>CC(opr)</sub> = C<sub>PD</sub> × V<sub>CC</sub> × f<sub>IN</sub> + I<sub>CC</sub>

TEST CIRCUIT



$C_L = 15/50\text{pF}$  or equivalent (includes jig and probe capacitance)  
 $R_1 = 1\text{K}\Omega$  or equivalent  
 $R_T = Z_{OUT}$  of pulse generator (typically  $50\Omega$ )

WAVEFORM: PROPAGATION DELAY ( $f=1\text{MHz}$ ; 50% duty cycle)



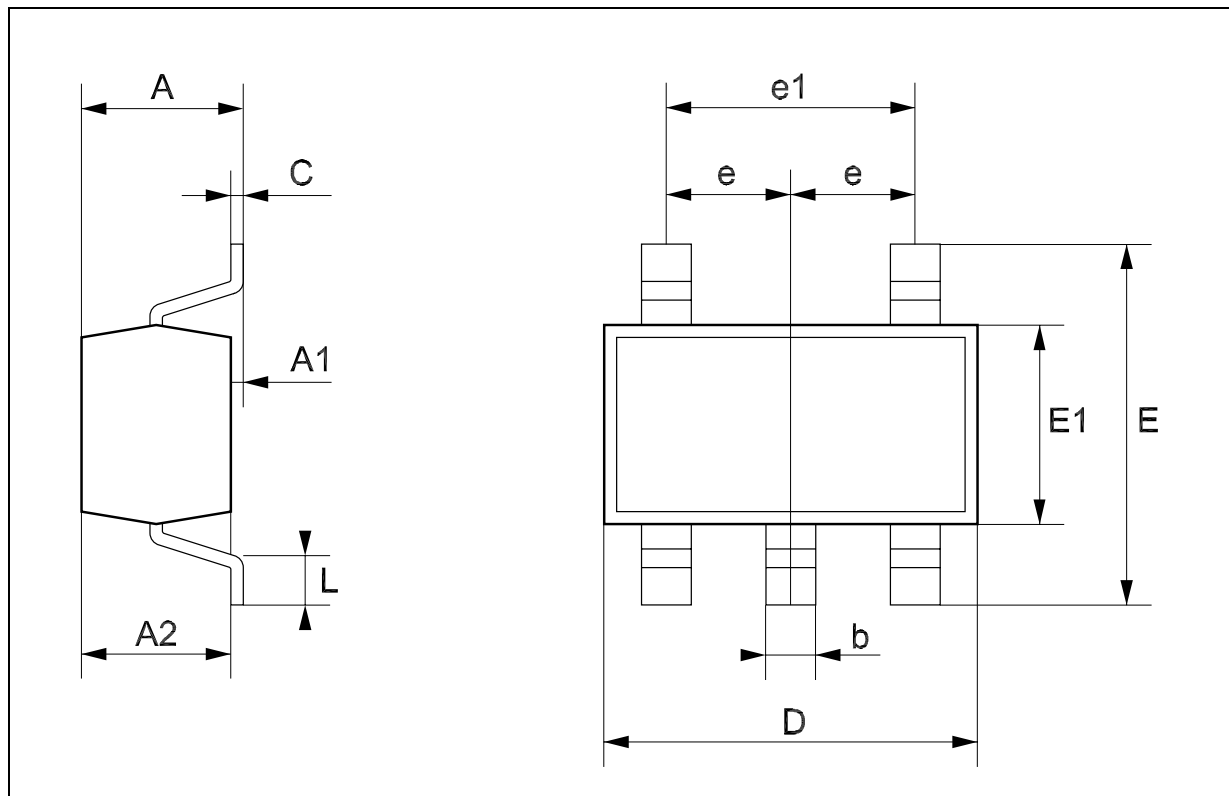
## SOT23-5L MECHANICAL DATA

DIM.	mm.			mils		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	0.90		1.45	35.4		57.1
A1	0.00		0.10	0.0		3.9
A2	0.90		1.30	35.4		51.2
b	0.35		0.50	13.7		19.7
C	0.09		0.20	3.5		7.8
D	2.80		3.00	110.2		118.1
E	1.50		1.75	59.0		68.8
e		0.95			37.4	
H	2.60		3.00	102.3		118.1
L	0.10		0.60	3.9		23.6



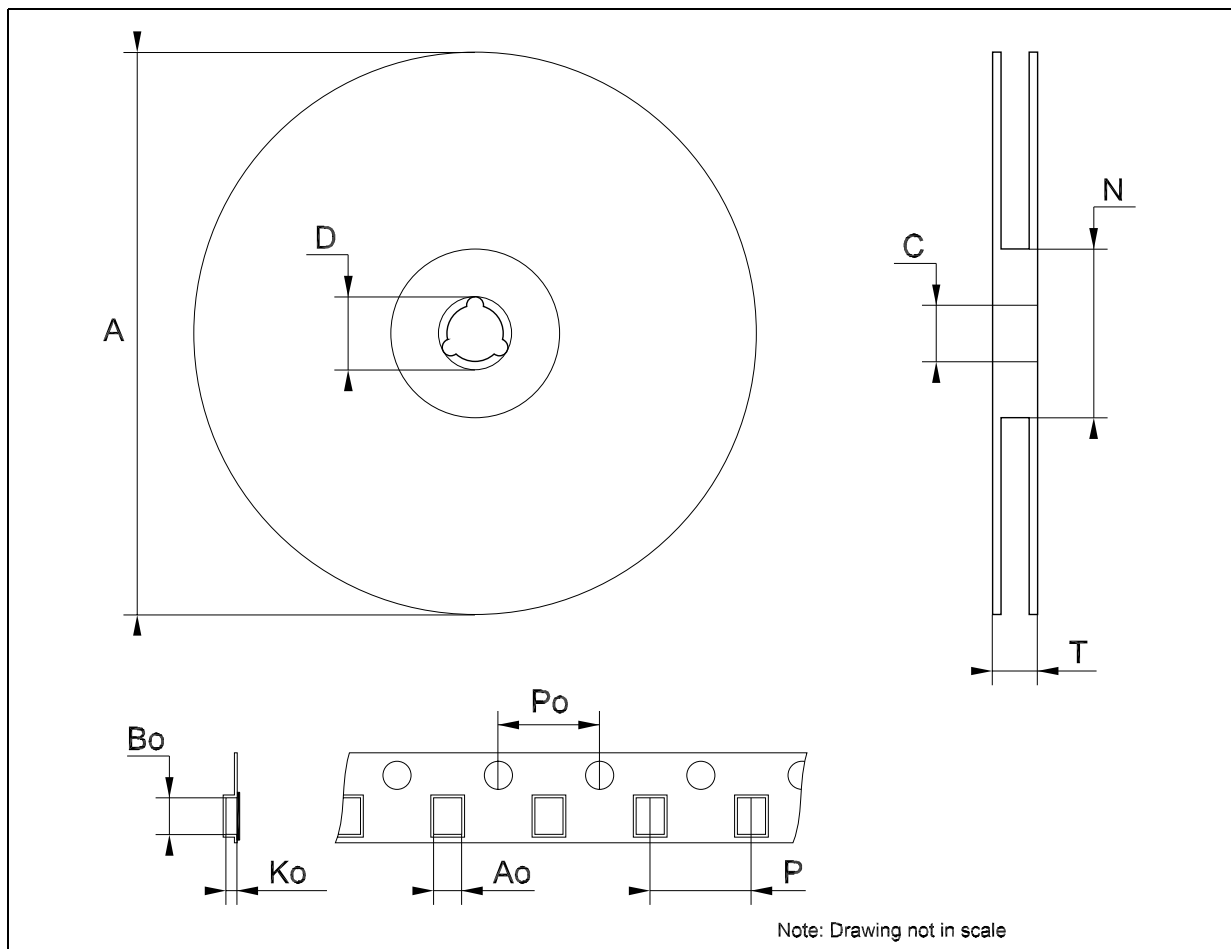
## SOT323-5L MECHANICAL DATA

DIM.	mm.			mils		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	0.80		1.10	31.5		43.3
A1	0.00		0.10	0.0		3.9
A2	0.80		1.00	31.5		39.4
b	0.15		0.30	5.9		11.8
C	0.10		0.18	3.9		7.1
D	1.80		2.20	70.9		86.6
E	1.80		2.40	70.9		94.5
E1	1.15		1.35	45.3		53.1
e		0.65			25.6	
e1		1.3			51.2	
L	0.10		0.30	3.9		11.8



## Tape &amp; Reel SOT23-xL MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A			180			7.086
C	12.8	13.0	13.2	0.504	0.512	0.519
D	20.2			0.795		
N	60			2.362		
T			14.4			0.567
Ao	3.13	3.23	3.33	0.123	0.127	0.131
Bo	3.07	3.17	3.27	0.120	0.124	0.128
Ko	1.27	1.37	1.47	0.050	0.054	0.058
Po	3.9	4.0	4.1	0.153	0.157	0.161
P	3.9	4.0	4.1	0.153	0.157	0.161



## Tape &amp; Reel SOT323-xL MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	175	180	185	6.889	7.086	7.283
C	12.8	13	13.2	0.504	0.512	0.519
D	20.2			0.795		
N	59.5	60	60.5		2.362	
T			14.4			0.567
Ao		2.25			0.088	
Bo		2.7			0.106	
Ko		1.2			0.047	
Po	3.9	4	4.1	0.153	0.157	0.161
P	3.8	4	4.2	0.149	0.157	0.165





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